

2SK3876-01R

N-CHANNEL SILICON POWER MOSFET

■ Outline Drawings (mm) 200407

FUJI POWER MOSFET Super FAP-G Series

■ Features

High speed switching, Low on-resistance
Low driving power, Avalanche-proof
No secondary breakdown

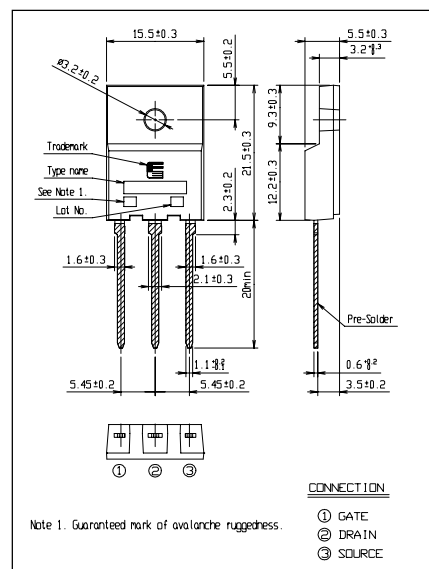
■ Applications

Switching regulators
UPS (Uninterruptible Power Supply)
DC-DC converters

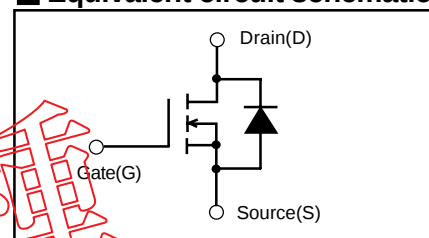
■ Maximum ratings and characteristic

● Absolute maximum ratings (Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit	Remarks
Drain-source voltage	V _{DS}	900	V	
	V _{DSX}	900	V	V _{GS} =-30V
Continuous Drain Current	I _D	13	A	
Pulsed Drain Current	I _{D(puls)}	±52	A	
Gate-Source Voltage	V _{GS}	±30	V	
Non-Repetitive Maximum Avalanche current	I _{AS}	13	A	Note *1
Repetitive Maximum Avalanche current	I _{AR}	6.5	A	Note *2
Non-Repetitive Maximum Avalanche Energy	E _{AS}	1006	mJ	Note *3
Repetitive Maximum Avalanche Energy	E _{AR}	17.0	mJ	Note *4
Maximum Drain-Source dV/dt	dV _{DS} /dt	40	kV/μs	V _{DS} ≤ 900V
Peak Diode Recovery dV/dt	dV _{DR} /dt	5	kV/μs	Note *4
Max. Power Dissipation	P _D	170	W	Tc=25°C
Operating and Storage Temperature range	T _{ch} T _{stg}	-55 to +150	°C	Ta=25°C
Isolation Voltage	V _{ISO}	2	kVrms	t=60sec f=60Hz



■ Equivalent circuit schematic



Note *1: T_{ch} ≤ 150°C

Note *2: Starting T_{ch}=25°C, I_{AS}=5.2A, L=67.5mH,

V_{GS}=100V, R_G=50Ω

E_{AS} limited by maximum channel temperature and Avalanche current.

See to the 'Avalanche Energy' graph

Note *3: Repetitive rating; Pulse width limited by maximum channel temperature.

See to the 'Transient Thermal impedance' graph.

Note *4: I_{AS} ≤ -I_D, -di/dt=50A/μs, V_{CC} ≤ BV_{DSS}, T_{ch} ≤ 150°C

● Electrical characteristics (Tc =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA V _{GS} =0V	900			V
Gate Threshold Voltage	V _{GS(th)}	I _D =250μA V _{DS} =V _{GS}	3.0		5.0	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =900V V _{GS} =0V T _{ch} =25°C			25	μA
		V _{DS} =720V V _{GS} =0V T _{ch} =125°C			250	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V V _{DS} =0V			100	nA
Drain-Source On-State Resistance	R _{DS(on)}	I _D =6.5A V _{GS} =10V		0.79	1.00	Ω
Forward Transconductance	g _{fs}	I _D =6.5A V _{DS} =25V	6.0	12		S
Input Capacitance	C _{iss}	V _{DS} =25V V _{GS} =0V		1750	2625	pF
Output Capacitance	C _{oss}	f=1MHz		220	330	pF
Reverse Transfer Capacitance	C _{rss}			13	19.5	pF
Turn-On Time t _{on}	t _{d(on)}	V _{CC} =600V I _D =6.5A		20	30	ns
		V _{GS} =10V		12	18	ns
Turn-Off Time t _{off}	t _{d(off)}	R _{GS} =10Ω		60	90	ns
				15	22.5	ns
Total Gate Charge	Q _G	V _{CC} =450V I _D =13A V _{GS} =10V		46	69	nC
Gate-Source Charge	Q _{GS}			14	21	nC
Gate-Drain Charge	Q _{GD}			17	26	nC
Diode forward on-voltage	V _{SD}	I _F =13A V _{GS} =0V T _{ch} =25°C		1.10	1.50	V
Reverse recovery time	t _{rr}	I _F =13A V _{GS} =0V		4.5		μs
Reverse recovery charge	Q _{rr}	-di/dt=100A/μs T _{ch} =25°C		25		μC

● Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-c)}	channel to case			0.735	°C/W
	R _{th(ch-a)}	channel to ambient			40.0	°C/W

Characteristics

